

## Lecture 27m: Noise &amp; MDS

**Example: TransR Amplifier Noise (cont)**

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- To summarize, for a transresistance amplifier, the equivalent input-referred current and voltage noise generators are given by:

$$\overline{i_{eq}^2} = \overline{i_{ia}^2} + \overline{i_f^2} + \frac{\overline{v_{ia}^2}}{R_f^2}$$

$$\overline{v_{eq}^2} = \overline{v_{ia}^2}$$

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**LF356 Op Amp Data Sheet**

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### LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

#### General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (Bi-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

#### Common Features

- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High Input Impedance:  $10^{12}\Omega$
- Low Input noise current:  $0.01\text{ pA}/\sqrt{\text{Hz}}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

#### Features

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

#### Uncommon Features

	LF155/ LF355	LF156/ LF256	LF257/ LF357	Units
Extremely fast settling time to 0.01%	4	1.5	1.5	μs
Fast slew rate	5	12	50	V/μs
Wide gain bandwidth	2.5	5	20	MHz
Low Input noise voltage	20	12	12	nV/√Hz

$\overline{i_{ia}^2} = 0.01\text{ pA}/\sqrt{\text{Hz}}$

$\overline{v_{ia}^2} = 12\text{ nV}/\sqrt{\text{Hz}}$

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**Example ARW Calculation**

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- Example Design:**
  - Sensor Element:**  
 $m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg/m}^3) = 4.6 \times 10^{-10}\text{kg}$   
 $\omega_s = 2\pi(15\text{kHz})$   
 $\omega_d = 2\pi(10\text{kHz})$   
 $k_s = \omega_s^2 m = 4.09 \text{ N/m}$   
 $x_d = 20 \mu\text{m}$   
 $Q_s = 50,000$   
 $V_p = 5\text{V}$   
 $h = 20 \mu\text{m}$   
 $d = 1 \mu\text{m}$
  - Sensing Circuitry:**  
 $R_f = 100\text{k}\Omega$   
 $i_{ia} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$   
 $v_{ia} = 12 \text{ nV}/\sqrt{\text{Hz}}$

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**Example ARW Calculation (cont)**

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Get rotation rate to output current scale factor:

$$A = 2 \frac{\omega_d}{\omega_s} Q_s \eta_e |\Theta(j\omega_d)| = 2 \left( \frac{10\text{K}}{15\text{K}} \right) (50\mu\text{s}) (5) (2000\epsilon_0) / (0.000024) = 2.83 \times 10^{-12} \text{ C}$$

$$\Theta(j\omega_d) = \frac{(j\omega_d)(\omega_s/\omega_d)}{-\omega_d^2 + j\omega_d\omega_s + \omega_s^2} = \frac{j(10\text{K})(15\text{K})/(50\mu\text{s})}{(15\text{K})^2 - (10\text{K})^2 + j(10\text{K})(15\text{K})/50\mu\text{s}} = \frac{j(3\text{K})}{1.25 \times 10^8 + j(3\text{K})}$$

$$\rightarrow |\Theta(j\omega_d)| = \frac{3\text{K}}{\sqrt{(1.25 \times 10^8)^2 + (3\text{K})^2}} = 0.000024 \quad 8.854 \times 10^{-8} \text{ F/m}$$

$$\left[ \frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h W_p}{d} = \frac{\epsilon_0 (20\mu\text{m})(100\mu\text{m})}{(1\mu\text{m})^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = 5(2000\epsilon_0) \quad 8.854 \times 10^{-12} \text{ F/m} \right]$$

Assume electrode covers the whole sidewall.

Then, get noise:

$$\frac{\overline{i_{eq}^2}}{\delta f} = \frac{4kT}{R_x} |\Theta(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{i_{ia}^2}{\delta f} + \frac{\overline{v_{ia}^2}}{\delta f} \left( \frac{1}{R_f^2} \right)$$

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**Example ARW Calculation (cont)**

$$R_{\text{RF}} = \frac{\omega_s m}{Q_s \eta_e} = \frac{2\pi(15K)(4.6 \times 10^{-10})}{(50k)(2.85 \times 10^{-9})^2} = 110.6 \text{ k}\Omega$$

$$\frac{i_{\text{eq,TOT}}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6k)} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$\rightarrow 8.64 \times 10^{-25} A^2/\text{Hz}$        $1.66 \times 10^{-26} A^2/\text{Hz}$        $1 \times 10^{-28} A^2/\text{Hz}$        $1.44 \times 10^{-28} A^2/\text{Hz}$

Sensor element noise  
Insignificant

Noise from  $R_f$  dominates!

$$\therefore \frac{i_{\text{eq,TOT}}^2}{\Delta f} = 1.68 \times 10^{-26} A^2/\text{Hz} \rightarrow i_{\text{eq,TOT}} = \sqrt{\frac{i_{\text{eq,TOT}}^2}{\Delta f}} = 1.30 \times 10^{-13} A/\sqrt{\text{Hz}}$$

$$\therefore S2_{\text{min}} = \frac{i_{\text{eq,TOT}}}{A} \left( \frac{3600\pi}{\text{hr}} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-12}} (3600) \left( \frac{180}{\pi} \right) = 9448 (\%/\text{hr})/\sqrt{\text{Hz}}$$

And finally:

$$\text{ARW} = \frac{1}{60} S2_{\text{min}} = \frac{1}{60} (9448) = 157 \%/\text{hr} = \text{ARW}$$

$\Rightarrow$  Almost turned around in 1 hour!

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**What if  $\omega_d = \omega_s$ ?**

If  $\omega_d = \omega_s = 15\text{kHz}$ , then  $|H(j\omega_d)| = 1$  and

$$A = 2 \frac{\omega_d}{\omega_s} Q_s X_d \eta_e |H(j\omega_d)| = 2 Q_s X_d \eta_e = 2(50k)(20\mu)(5)(2000\epsilon_0) = 1.77 \times 10^{-7} \text{ C}$$

$$\frac{i_{\text{eq,TOT}}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6k)} (1)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$\rightarrow 1.51 \times 10^{-25} A^2/\text{Hz}$        $1.66 \times 10^{-26} A^2/\text{Hz}$        $1 \times 10^{-28} A^2/\text{Hz}$        $1.44 \times 10^{-28} A^2/\text{Hz}$

Now, the sensor element dominates!

$$\therefore \frac{i_{\text{eq,TOT}}^2}{\Delta f} = 1.67 \times 10^{-25} A^2/\text{Hz} \rightarrow i_{\text{eq,TOT}} = \sqrt{\frac{i_{\text{eq,TOT}}^2}{\Delta f}} = 4.08 \times 10^{-13} A/\sqrt{\text{Hz}}$$

$$\therefore S2_{\text{min}} = \frac{i_{\text{eq,TOT}}}{A} \left( \frac{3600\pi}{\text{hr}} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left( \frac{180}{\pi} \right) = 0.476 (\%/\text{hr})/\sqrt{\text{Hz}}$$

And finally:

$$\text{ARW} = \frac{1}{60} S2_{\text{min}} = \frac{1}{60} (0.476) = 0.0079 \%/\text{hr} = \text{ARW}$$

$\Rightarrow$  Navigation grade!

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